

REMARKS

Applicants wish to thank Examiner Zimmer for indicating allowability of Claim 4 if rewritten in independent form including all of the limitations of the base claim and any intervening claims.

Applicants respectfully request reconsideration of the application, as amended, in view of the following remarks.

The rejection of Claims 1 and 2 under 35 U.S.C. § 102(b) as anticipated by JP 2002-155143 is respectfully traversed.

JP 2002-155143 discloses in paragraph [0001] a borazine-containing silicon-based polymer useful as a coating film exhibiting high burning resistance and high heat resistance. However, JP 2002-155143 fails to disclose an insulating material for insulating layers between electric wirings as claimed in Claims 1 and 2. In addition, JP 2002-155143 fails to disclose or suggest an insulating layer as claimed in **new Claims 5 and 6** or an ultra large scale integrated circuit (ULSI) as claimed in **new Claims 7 and 8**.

The polymer material of the present invention is advantageously used as an interlayer insulation film for multilayer connection and to suppress an increase of the parasitic capacity between wiring layers due to the growth of the degree of integration of an ultra-large-scale integration (ULSI). As a result, the semiconductor device can give a high-speed operation (see for example, paragraphs [0046] and [0232] of the specification).

Therefore, the rejection of Claims 1 and 2 under 35 U.S.C. § 102(b) as anticipated by JP 2002-155143 is believed to be unsustainable as the present invention is neither anticipated nor obvious and withdrawal of this rejection is respectfully requested.

The rejection of Claim 1 under 35 U.S.C. § 102(b) as anticipated by The Abstract (The 62nd Autumn Meeting of The Japan Society of Applied Physics, 2001, p. 656) is respectfully traversed.

The Abstract (The 62nd Autumn Meeting of The Japan Society of Applied Physics, 2001, p. 656) fails to disclose an insulating material for insulating layers between electric wirings as claimed in Claims 1 and 2. In addition, The Abstract (The 62nd Autumn Meeting of The Japan Society of Applied Physics, 2001, p. 656) fails to disclose or suggest an insulating layer as claimed in **new Claims 5 and 6** or an ultra large scale integrated circuit (ULSI) as claimed in **new Claims 7 and 8**.

The Abstract (The 62nd Autumn Meeting of The Japan Society of Applied Physics, 2001, p. 656) discloses a chemical formula of a copolymer resulting from a borazine which is different from the borazine compound of Claim 1 (formula 1). Note that R3 in formula 1 of Claim 1 is an alkyl group linked to an acetylene group. In formula (I) of The Abstract, there is no alkyl group linked to an acetylene group.

Thus, The Abstract does not disclose or suggest a copolymer obtained by polymerization of the borazine compound represented by chemical formula 1 and the organic silicon compound represented by chemical formula 2 as claimed in claim 1.

Therefore, the rejection of Claim 1 under 35 U.S.C. § 102(b) as anticipated by The Abstract (The 62nd Autumn Meeting of The Japan Society of Applied Physics, 2001, p. 656) is believed to be unsustainable as the present invention is neither anticipated nor obvious and withdrawal of this rejection is respectfully requested.

The rejection of Claim 1 under 35 U.S.C. § 102(b) as anticipated by Inoe et al is respectfully traversed.

Inoe et al fail to disclose an insulating material for insulating layers between electric wirings as claimed in Claims 1 and 2. In addition, Inoe et al fail to disclose or suggest an insulating layer as claimed in **new Claims 5 and 6** or an ultra large scale integrated circuit (ULSI) as claimed in **new Claims 7 and 8**.

Inoe et al discloses a chemical formula of a copolymer resulting from a borazine which is different from the borazine compound of Claim 1 (formula 1). Note that R3 in formula 1 of Claim 1 is an alkyl group linked to an acetylene group. In the borazine formula of Inoe et al, there is no alkyl group linked to an acetylene group.

Thus, Inoe et al does not disclose or suggest a copolymer obtained by polymerization of the borazine compound represented by chemical formula 1 and the organic silicon compound represented by chemical formula 3 as claimed in claim 1.

Therefore, the rejection of Claim 1 under 35 U.S.C. § 102(b) as anticipated by Inoe et al is believed to be unsustainable as the present invention is neither anticipated nor obvious and withdrawal of this rejection is respectfully requested.

The provisional double patenting rejection of Claim 1 over claims 9, 10, 11 and 12 of copending application Serial No. 10/529,369 is traversed.

U.S. Application Serial No. 10/529,369 relates to a method for producing a borazine-based resin and is characterized in that the method includes the step of removing a solid catalyst or metal catalyst that have been added during the course of the production. Another feature relies on a composite insulating film that comprises a first insulating film of siloxane resin and a second insulating film of a borazine resin formed on the first insulating film.

Claims 9-12 of U.S. Application Serial No. 10/529,369 fail to disclose an insulating material for insulating layers between electric wirings as claimed in Claims 1 and 2. In addition, Inoe et al fail to disclose or suggest an insulating layer as claimed in **new Claims 5**

Application No.: 10/809,704
Reply to Office Action of: June 14, 2007

and 6 or an ultra large scale integrated circuit (ULSI) as claimed in **new Claims 7 and 8**.

Thus, this rejection should be withdrawn.

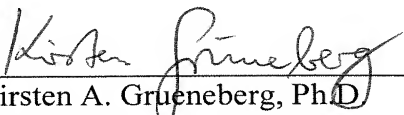
This application presents allowable subject matter, and the Examiner is kindly requested to pass it to issue. Should the Examiner have any questions regarding the claims or otherwise wish to discuss this case, he is kindly invited to contact Applicants' below-signed representative, who would be happy to provide any assistance deemed necessary in speeding this application to allowance.

Respectfully submitted,

OBLON, SPIVAK, McCLELLAND,
MAIER & NEUSTADT, P.C.
Norman F. Oblon

Customer Number
22850

Tel: (703) 413-3000
Fax: (703) 413 -2220
NFO:KAG:
(OSMMN 08/07)


Kirsten A. Grueneberg, PhD
Registration No.: 47,297